



Docket No.: M4065.0698/P698-A
(PATENT)

JFW

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:
Kristy A. Campbell et al.

Application No.: 10/736,617

Confirmation No.: 4072

Filed: December 17, 2003

Art Unit: 2829

For: METHOD OF FORMING NON-VOLATILE RESISTANCE VARIABLE DEVICES, METHOD OF FORMING A PROGRAMMABLE MEMORY CELL OF MEMORY CIRCUITRY, AND A NON-VOLATILE RESISTANCE VARIABLE DEVICE

Examiner: Victor V. Yevsikov

SUPPLEMENTAL REMARKS IN RESPONSE TO ADVISORY ACTION

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Dear Sir:

In response to the Advisory Action dated February 9, 2005, and further to Applicants' Request for Continued Examination dated February 4, 2005, please consider the following Supplemental Remarks.

SUPPLEMENTAL REMARKS

Applicants' Request for Continued Examination dated February 4, 2005, submitted for entry the Amendments filed on January 19, 2005. The January 19 Amendments included an amendment to claim 31 adding the limitation "and approximately no metal chalcogenide agglomerations at the interface." In the Advisory Action, the Examiner states that "the added language to 'no agglomerations' . . . is not discussed in the specification." Advisory Action at 2. Applicants respectfully disagree.